

wherein the wirings include at least one inert element, and 90% or more of the inert element is argon, and

wherein an amount of sodium contained within the wirings is equal to or less than 0.3 ppm.

Q1
Sub B3 3 (Amended). A semiconductor device according to claim 1, wherein electrical resistivity of the wirings is equal to or less than $40 \mu\Omega\cdot\text{cm}$.

4 (Amended). A semiconductor device comprising:

a metallic film formed over a substrate, the metallic film comprising one element, or a plurality of elements, selected from the group consisting of W, Ta, Ti, Mo, Cr, Nb, and Si; a metallic compound film having said elements as main constituents; an alloy film of a combination of said elements; or a lamination film of thin films selected from the group consisting of said metallic film, said metallic compound film, and said alloy film,

Q2 wherein the metallic film includes at least one inert element, and 90% or more of the inert element is argon, and

wherein an amount of sodium contained within the metallic film is equal to or less than 0.3 ppm.

5 (Amended). A device according to claim 4, further comprising a semiconductor film adjacent to the metallic film with an insulating film interposed therebetween.

6 (Amended). A device according to claim 4, wherein the inert element except for argon is contained within the metallic film at an amount equal to or less than 1 atom%.

7 (Amended). A device according to claim 4, wherein the inert element except for argon is contained within the metallic film at an amount equal to or less than 0.1 atom%.

Sub C17 8 (Amended). A device according to claim 4, wherein the inert element except for the argon
Sub B4 is Xe or Kr.

✓ 9 (Amended). A device according to claim 4, wherein internal stress of the metallic film is
from -1×10^{10} dyn/cm² to $+1 \times 10^{10}$ dyn/cm².

10 (Amended). A device according to claim 4, wherein line width of the metallic film is
equal to or less than 5 μ m.

11 (Amended). A device according to claim 4, wherein film thickness of the metallic film
is equal to or greater than 0.1 μ m, and equal to or less than 0.7 μ m.

12 (Amended). A device according to claim 4, wherein the metallic film is used as a gate
wiring of a TFT.

A2
cont. 13 (Amended). A device according to claim 4, wherein resistance value per 1 square μ m of
surface area of a connection between the metallic film and an aluminum wiring is equal to or less
than 40 Ω .

Sub C17 14 (Amended). A device according to claim 4, wherein the semiconductor device is selected
from the group consisting of an active matrix type liquid crystal display, an active matrix type EL
display, and an active matrix type EC display.

15 (Amended). A device according to claim 4, wherein the semiconductor device is at least
one electric device selected from the group consisting of a video camera, a digital camera, a
projector, a goggle type display, a car navigation system, a personal computer, and a portable
Sub B5 information terminal.

16 (Amended). A semiconductor device comprising:

a film formed over a substrate, the film comprising tungsten or a tungsten compound as a main constituent; and

an insulating film formed over the film, said insulating film comprising SiOxNy, wherein the film includes at least one inert element, and 90% or more of the inert element is argon, and

wherein an amount of sodium contained within the film is equal to or less than 0.3 ppm.

17 (Amended). A device according to claim 16, further comprising a semiconductor film adjacent to the film comprising tungsten with an insulating film interposed therebetween.

18 (Amended). A device according to claim 16, wherein the inert element except for argon is contained within the film at an amount equal to or less than 1 atom%.

19 (Amended). A device according to claim 16, wherein the inert element except for argon is contained within the film at an amount equal to or less than 0.1 atom%.

20 (Amended). A device according to claim 16, wherein the inert element except for argon is Xe or Kr.

21 (Amended). A device according to claim 16, wherein internal stress of the tungsten film or of the film comprising the tungsten compound as its main constituent is from -1×10^{10} dyn/cm² to $+1 \times 10^{10}$ dyn/cm².

22 (Amended). A device according to claim 16, wherein line width of the film is equal to or less than 5 μ m.

23 (Amended). A device according to claim 16, wherein the film thickness of the film is equal to or greater than 0.1 μ m, and equal to or less than 0.7 μ m.

24 (Amended). A device according to claim 16, wherein the film is used as a gate wiring of a TFT.

25 (Amended). A device according to claim 16, wherein resistance value per 1 square μm of surface area of a connection between the film and an aluminum wiring is equal to or less than 40 Ω .

SUB C1 7
26 (Amended). A device according to claim 16, wherein the semiconductor device is selected from the group consisting of an active matrix type liquid crystal display, an active matrix type EL display, and an active matrix type EC display.

27 (Amended). A device according to claim 16, wherein the semiconductor device is at least one electric device selected from the group consisting of a video camera, a digital camera, a projector, a goggle type display, a car navigation system, a personal computer, and a portable information terminal.

Sub B1
28 (Amended). A semiconductor device comprising:
a wiring formed over a substrate having a lamination structure comprising a film comprising tungsten or a tungsten compound as a main constituent, and a nitride film of tungsten,
wherein the film comprising tungsten includes at least one inert element, and 90% or more of the inert element is argon, and
wherein an amount of sodium contained within the wiring is equal to or less than 0.3 ppm.

SUB C1 7
29 (Amended). A device according to claim 28, wherein the wiring further comprises a semiconductor film adjacent to the wiring with an insulating film interposed therebetween.

30 (Amended). A device according to claim 28, wherein the inert element except for argon is contained within the wiring at an amount equal to or less than 1 atom%.

SUB C1.7
31 (Amended). A device according to claim 28, wherein the inert element except for argon is contained within the wiring at an amount equal to or less than 0.1 atom%.

A2
32 (Amended). A device according to claim 28, wherein the inert element except for argon is Xe or Kr.

33 (Amended). A device according to claim 28, wherein internal stress of the tungsten film or of the film having the tungsten compound as its main constituent is from -1×10^{10} dyn/cm² to $+1 \times 10^{10}$ dyn/cm².

38 (Amended). A device according to claim 28, wherein the semiconductor device is selected from the group consisting of an active matrix type liquid crystal display, an active matrix type EL display, and an active matrix type EC display.

39 (Amended). A device according to claim 28, wherein the semiconductor device is at least one electric device selected from the group consisting of a video camera, a digital camera, a projector, a goggle type display, a car navigation system, a personal computer, and a portable information terminal.

3 Sub B4
✓ 40 (Amended). A semiconductor device comprising:

a wiring formed over a substrate, the wiring having a lamination structure containing a silicon film having an added impurity element for imparting conductivity, a film comprising tungsten or a tungsten compound as a main constituent, and a nitride film of tungsten,

wherein the film comprising tungsten includes at least one inert element, and 90% or more of the inert element is argon, and

wherein an amount of sodium contained within the wiring is equal to or less than 0.3 ppm.

41 (Amended). A device according to claim 40, further comprising a semiconductor film adjacent to the wiring with an insulating film interposed therebetween.

42 (Amended). A device according to claim 40, wherein the inert element except for argon is contained within the wiring at an amount equal to or less than 1 atom%.

43 (Amended). A device according to claim 40, wherein the inert element except for argon is contained within the wiring at an amount equal to or less than 0.1 atom%.

44 (Amended). A device according to claim 40, wherein the inert element except for argon is Xe or Kr.

45 (Amended). A device according to claim 40, wherein internal stress of the tungsten film or of the film having the tungsten compound as its main constituent is from -1×10^{10} dyn/cm² to $+1 \times 10^{10}$ dyn/cm².

50 (Amended). A device according to claim 40, wherein the semiconductor device is selected from the group consisting of an active matrix type liquid crystal display, an active matrix type EL display, and an active matrix type EC display.

51 (Amended). A device according to claim 40, wherein the semiconductor device is at least one electric device selected from the group consisting of a video camera, a digital camera, a projector, a goggle type display, a car navigation system, a personal computer, and a portable information terminal.

52 (Amended). A semiconductor device comprising:
a wiring comprising tungsten formed over a substrate,
wherein the wiring includes at least one inert element, and 90% or more of the inert element is argon,